

AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

LISTING OF CLAIMS:

1. (Currently amended) A CMP abrasive ~~for polishing an inorganic insulating film having unevenness on a surface thereof~~, consisting essentially of cerium oxide particles, a dispersant, water, and, additionally, an organic polymer having an atom or a structure capable of forming a hydrogen bond with a hydroxyl group present on a surface of said film to be polished, wherein the organic polymer is a compound containing at least one atom having an unpaired electron in a molecular structure, and wherein the abrasive is capable of being used in forming shallow trench isolation, and is adapted to polish an inorganic insulating film having unevenness on a surface thereof.

2. (Cancelled).

3. (Currently amended) The CMP abrasive ~~for polishing an inorganic insulating film having unevenness on a surface thereof~~ according to Claim 1, wherein said organic polymer is a compound containing either one or both of a nitrogen atom and an oxygen atom in a molecular structure.

4. (Currently amended) The CMP abrasive ~~for polishing an inorganic insulating film having unevenness on a surface thereof~~ according to Claim 1, wherein said organic polymer is a compound having an adsorption ratio of 50% or more with

respect to silicon oxide particles of a specific surface area of $50 \text{ m}^2/\text{g}$ dispersed in water of pH 6 to 8.

5. (Currently amended) The CMP abrasive ~~for polishing an inorganic insulating film having unevenness on a surface thereof~~ according to Claim 1, wherein said organic polymer is a compound having an adsorption ratio of 40% or more with respect to silicon nitride particles of a specific surface area of $3.3 \text{ m}^2/\text{g}$ dispersed in water of pH 6 to 8.

6. (Currently amended) The CMP abrasive ~~for polishing an inorganic insulating film having unevenness on a surface thereof~~ according to Claim 1, wherein the sedimentation speed of the cerium oxide particles is $20 \text{ }\mu\text{m/s}$ or less.

7. (Currently amended) The CMP abrasive ~~for polishing an inorganic insulating film having unevenness on a surface thereof~~ according to Claim 1, wherein said organic polymer is polyvinyl pyrrolidone.

8. (Currently amended) The CMP abrasive ~~for polishing an inorganic insulating film having unevenness on a surface thereof~~ according to Claim 7, wherein said polyvinyl pyrrolidone has a weight average molecular weight of 5,000 to 1,200,000.

9. (Currently amended) The CMP abrasive ~~for polishing an inorganic insulating film having unevenness on a surface thereof~~ according to Claim 1, which comprises 0.01 to 2.0 parts by weight of a dispersant and 0.001 to 1,000 parts by

weight of an organic polymer based on the cerium oxide particle of 100 parts by weight, and the rest comprising water, the concentration of the cerium oxide particles in the abrasive being 0.5 to 20% by weight.

10. (Withdrawn) A method for polishing a substrate comprising polishing by moving a substrate on which an inorganic insulating film having unevenness on a surface thereof, to be polished is formed and a polishing platen while pressing the substrate against the polishing platen and a polishing cloth and supplying said CMP abrasive for polishing the inorganic insulating film having unevenness on a surface thereof according to Claim 1, between the inorganic insulating film to be polished and the polishing cloth.

11. (Withdrawn) A method for manufacturing a semiconductor device comprising a step of polishing an inorganic insulating film having unevenness on a surface thereof, to be polished, by moving a substrate on which the film to be polished is formed and a polishing platen while pressing the substrate against the polishing platen and a polishing cloth and supplying said CMP abrasive for polishing an inorganic insulating film having unevenness on a surface thereof according to Claim 1, between the inorganic insulating film to be polished and the polishing cloth.

12.-26. (Cancelled).

27. (Currently amended) The CMP abrasive ~~for polishing inorganic insulating films having unevenness on a surface thereof~~ according to Claim 1, wherein said dispersant is selected from the group consisting of water-soluble

anionic dispersants, water-soluble nonionic dispersants, water-soluble cationic dispersants and water-soluble amphoteric dispersants.

28. (Currently amended) The CMP abrasive ~~for polishing inorganic insulating films having unevenness on a surface thereof~~ according to Claim 1, wherein said organic polymer is included in an amount of 0.01 part by weight to 100 parts by weight, based on 100 parts by weight of cerium oxide particles.

29. (Currently amended) The CMP abrasive ~~for polishing inorganic insulating films having unevenness on a surface thereof~~ according to Claim 1, consisting of the cerium oxide particles, the dispersant, water and the organic polymer.

30. (New) The CMP abrasive according to Claim 1, wherein the cerium oxide particles have an average particle diameter of 0.01 μ m to 1.0 μ m.

31. (New) The CMP abrasive according to Claim 1, wherein said organic polymer is selected from the group consisting of poly (meth) acrylic acid ammonium salts.

32. (New) The CMP abrasive according to Claim 1, wherein said organic polymer is selected from the group consisting of poly (meth) acrylic acid derivatives.

33. (New) The CMP abrasive according to Claim 1, wherein said CMP abrasive is adapted to polish an oxide insulating film having unevenness on a surface thereof.

34. (New) The CMP abrasive according to Claim 1, wherein said CMP abrasive is adapted to polish a silicon oxide film having unevenness on a surface thereof.